**Product data sheet** 

## 1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO220 plastic package.





## 2. Features and benefits

- Trench structure
- High junction temperature up to 150°C
- Low forward voltage drop
- Negligible switching losses
- High efficiency

## 3. Applications

- · DC to DC converters
- · Freewheeling diode
- OR-ing diode

## 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			1	00		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 135 °C; per diode; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	15			А	
I <sub>O(AV)</sub>	average output current	$\delta$ = 0.5 ; square-wave pulse; $T_{mb} \le$ 134 °C; both diodes conducting	30			А	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
$V_{F}$	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>		-	0.58	0.63	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>		-	0.55	0.6	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>		-	0.66	0.71	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>		-	0.62	0.67	V
I <sub>R</sub>	reverse current	$V_R = 100 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; $ Fig. 7; Fig. 8		-	-	50	μΑ
		$V_R = 100 \text{ V}; T_j = 125 \text{ °C}; \text{ per diode}; $ Fig. 7; Fig. 8		-	-	30	mA

## 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode	<del>                                     </del>	A1 A2
3	A2	anode 2		Κ Κ sym125
mb	К	mounting base; connected to cathode		<b>y</b> ,2

## 6. Ordering information

**Table 3. Ordering information** 

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WN3S30H100C	TO220	WN3S30H100CQ	Tube	50	SOT78	13-Jun-2008

## 7. Marking

### **Table 4. Marking codes**

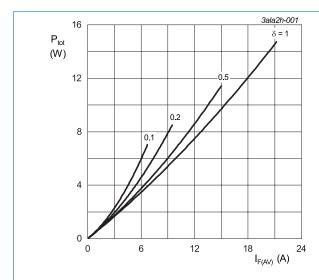
Type number	Marking codes
WN3S30H100C	WN3S 30H100C

## 8. Limiting values

### Table 5. Limiting values

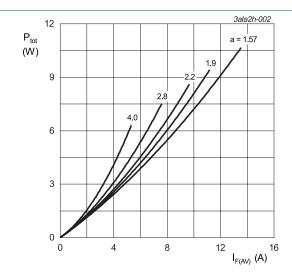
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		100	V
$V_{RWM}$	crest working reverse voltage		100	V
$V_R$	reverse voltage	DC	100	V
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 135$ °C; per diode; Fig. 1; Fig. 2; Fig. 3	15	А
$I_{O(AV)}$	average output current	$δ$ = 0.5 ; square-wave pulse; $T_{mb} \le 134$ °C; both diodes conducting	30	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	330	Α
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	363	Α
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		150	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$   $V_0 = 0.532 \text{ V}; R_s = 0.0077 \Omega$ Fig. 1. Forward power dissipation

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor =  $I_{F(RMS)}$  /  $I_{F(AV)}$  V<sub>o</sub> = 0.532 V; R<sub>s</sub> = 0.0077  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

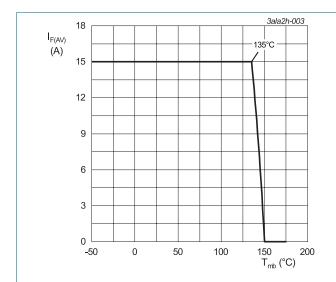


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

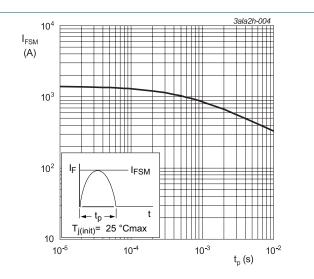


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	per diode; <u>Fig. 5</u>	-	-	1.3	K/W
	from junction to mounting base	both diodes conducting	-	-	0.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

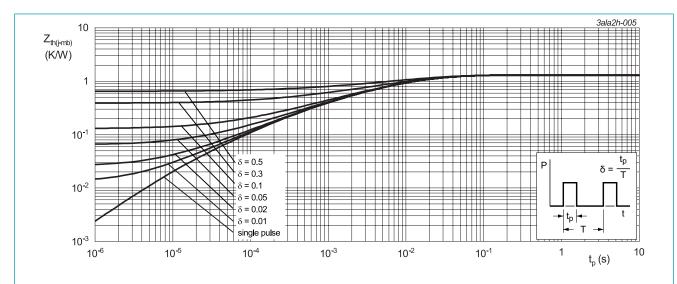
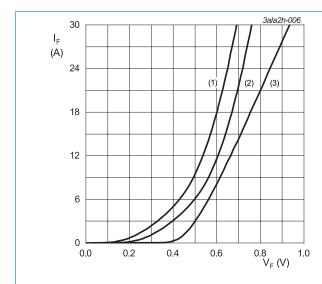


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 5 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>	-	0.49	0.55	V
		I <sub>F</sub> = 5 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>	-	0.43	0.48	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>	-	0.58	0.63	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>	-	0.55	0.6	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; per diode; <u>Fig. 6</u>	-	0.66	0.71	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 125 °C; per diode; <u>Fig. 6</u>	-	0.62	0.67	V
I <sub>R</sub>	reverse current	$V_R = 100 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; $ Fig. 7; Fig. 8	-	-	50	μΑ
		V <sub>R</sub> = 100 V; T <sub>j</sub> = 125 °C; per diode; Fig. 7; Fig. 8	-	-	30	mA

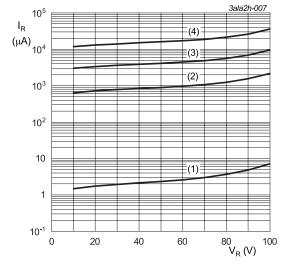


 $V_o = 0.532 \text{ V}; R_s = 0.0077 \Omega$ 

(1) T<sub>i</sub> = 150 °C; typical values (2) T<sub>i</sub> = 150 °C; maximum values

(3)  $T_i = 25$  °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode

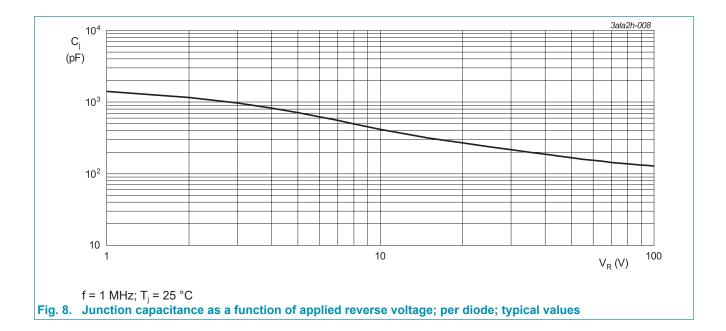


(1) T<sub>i</sub> = 25 °C; typical values

(2)  $T_j = 100 \,^{\circ}\text{C}$ ; typical values (3)  $T_j = 125 \,^{\circ}\text{C}$ ; typical values

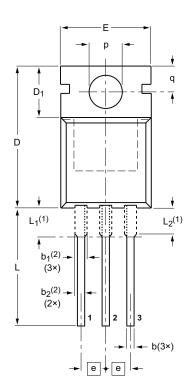
(4) T = 150 °C; typical values

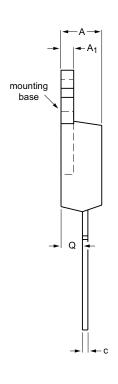
Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values



## 11. Package outline







0 5 10 mm scale

### **DIMENSIONS** (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> <sup>(2)</sup>	b <sub>2</sub> <sup>(2)</sup>	С	D	D <sub>1</sub>	E	е	L	L <sub>1</sub> <sup>(1)</sup>	L <sub>2</sub> <sup>(1)</sup> max.	р	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

### Notes

- 1. Lead shoulder designs may vary.
- Dimension includes excess dambar.

OUTLINE		REFER	REFERENCES EUROPEAN			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT78		3-lead TO-220AB	SC-46			<del>08-04-23</del> 08-06-13

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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